

Product Overview

SGF5N150UF: IGBT, Discrete, High Performance

For complete documentation, see the data sheet.

Fairchild's Insulated Gate Bipolar Transistor (IGBT) provides low conduction and switching losses. SGF5N150UF is designed for the switching power supply applications.

Features

- High Speed Switching
- Low Saturation Voltage : $V_{CE(sat)} = 4.7 \text{ V @ } I_C = 5 \text{ A}$
- High Input Impedance

Applications

- Other Industrial

Part Electrical Specifications

Product	Compliance	Status	$V_{ES}^{(BR)C}$ Typ (V)	I_C Max (A)	$V_{CE(sat)}$ Typ (V)	V_F Typ (V)	E_{off} Typ (mJ)	E_{on} Typ (mJ)	T_{rr} Typ (ns)	I_{rr} Typ (A)	Gate Charge Typ (nC)	Short Circuit Withstand (μ s)	E_{AS} Typ (mJ)	P_D Max (W)	Co- Pack aged Diode	Pack age Type
SGF5N150UFTU	Pb-free	Active	1500	10	4.7	-	0.1	0.19	-	-	30	-	-	62.5	No	TO-3PF-3L

For more information please contact your local sales support at www.onsemi.com.

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